

Product Introduction

Our InP (Indium Phosphide) wafers are grown using the Vertical Gradient Freeze (VGF) method, available in 2", 3", and 4" sizes with <100> orientation. Offered in undoped and doped variants (N-type: S, Sn;P-type: Zn), these epi-ready wafers feature low TTV ($\leq 15\mu\text{m}$), bow ($\leq 15\mu\text{m}$), and warp ($\leq 15\mu\text{m}$) for consistent downstream epitaxial growth. With polished or etched surface options, our InP wafers are well suited for photonic and optoelectronic device fabrication.

Applications

- Laser diodes and photodetectors for optical communication
- High-frequency and high-electron-mobility transistors (HEMT/HBT)
- Photonic integrated circuits
- Solar cell substrates for multi-junction cells

INDIUM PHOSPHIDE (INP) SPECIFICATIONS			
GROWTH METHOD	VGF		
Type/Dopant	Undoped // N/S/Sn // P/Zn		
Size	2inch	3inch	4inch
Diameter (mm)	50.8±0.3	76.2±0.3	100±0.3
Thickness (um)	350±25	625±25	625±25
OF(mm)	16±2	22±2	32.5±2
IF(mm)	8±2	12±2	18±2
Orientation	(100)±0.5		
TTV(um)	≤10	≤15	≤15
Bow(um)	≤15	≤15	≤15
Wrap(um)	≤15	≤15	≤15
Surface	Polished/Etched		
Epi-ready	Yes		